

**Amendments to the Claims**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently amended) A semiconductor device, comprising:  
a semiconductor substrate including an integrated circuit and an electrode;  
a passivation film having an opening which exposes a part of the electrode formed on a side of the semiconductor substrate where the electrode is formed;  
~~a resin layer provided on a side of the semiconductor substrate where the electrode is formed~~ the passivation film; and  
a wiring layer formed on an area reaching from the electrode to a top of the resin layer,  
wherein the electrode has a first rim part facing a periphery of the semiconductor substrate and a second rim part facing a center region of the semiconductor substrate, and  
wherein the resin layer is formed so as to overlap the second rim part, leaving out an area from the periphery of the semiconductor substrate to the first rim part of the electrode.
2. (Canceled)
3. (Original) The semiconductor device according to claim 2, wherein the resin layer is formed leaving out the exposed part by the opening of the electrode.
4. (Original) The semiconductor device according to claim 2, wherein a center of the opening is positioned so as to deviate from a center of the electrode towards the periphery of the semiconductor substrate.
5. (Original) A circuit board, where the semiconductor device according to claim 1 is mounted.
6. (Original) An electronic equipment, having the semiconductor device according to claim 1.
- 7-10. (Canceled)

11. (Currently amended) A semiconductor device, comprising:  
means for accommodating an integrated circuit and an electrode;  
a passivation film having an opening which exposes a part of the electrode  
formed on a side of the means for accommodating where the electrode is formed;

~~a resin layer provided on a side of the semiconductor substrate where the~~  
~~electrode is formed~~ the passivation film; and

a wiring layer formed on an area reaching from the electrode to a top of the  
resin layer,

wherein the electrode has a first rim part facing a periphery of the means for  
accommodating and a second rim part facing a center region of the means for  
accommodating, and

wherein the resin layer is formed so as to overlap the second rim part, leaving  
out an area from the periphery of the means for accommodating to the first rim part  
of the electrode.

12. (Original) The semiconductor device according to claim 1, further  
comprising a plurality of external terminals electrically connected to the wiring  
layer.

13. (Original) The semiconductor device according to claim 11, further  
comprising a plurality of external terminals electrically connected to the wiring  
layer.

14. (Canceled)

15. (Original) The semiconductor device according to claim 1, further  
comprising a resist layer covering a part of the wiring layer.

16. (Original) The semiconductor device according to claim 11, further  
comprising a resist layer covering a part of the wiring layer.

17. (Canceled)

18. (Original) The semiconductor device according to claim 15, further  
comprising a coat layer formed on the resist layer.

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19. (Original) The semiconductor device according to claim 16, further comprising a coat layer formed on the resist layer.

20. (Canceled)